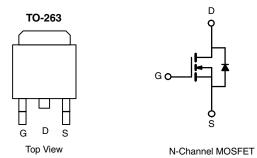


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Vishay Siliconix

# Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	100	
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0038	
I <sub>D</sub> (A)	120	
Configuration	Single	



#### **FEATURES**

- TrenchFET® Power MOSFET
- · Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R<sub>a</sub> and UIS Tested
- · Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N10-3m8-GE3

ABSOLUTE MAXIMUM RATINGS (To	c = 25 °C, unles	ss otherwise noted	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	100	V	
Gate-Source Voltage		$V_{GS}$	± 20	V	
Continuous Drain Currenta	T <sub>C</sub> = 25 °C	1	120		
Continuous Drain Currents	T <sub>C</sub> = 125 °C	l <sub>D</sub>	120		
Continuous Source Current (Diode Conduction) <sup>a</sup> Pulsed Drain Current <sup>b</sup>		Is	120	Α	
		I <sub>DM</sub>	480		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	73		
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	266	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C P <sub>D</sub> 375		375	W	
wiaximum Power Dissipation	T <sub>C</sub> = 125 °C	FD	125	VV	
Operating Junction and Storage Temperature Range	ge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.4	C/VV

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2 \,\%$ .
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



# Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	100	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.5	3.0	3.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 175 °C	-	-	500	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0030	0.0038	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0064	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0080	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		-	82	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	5780	7230	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	3070	3840	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	305	385	
Total Gate Charge <sup>c</sup>	Qg			-	125	190	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 70 \text{ A}$	-	28	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	1		-	46	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1.6	3.3	5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	16	25	
Rise Time <sup>c</sup>	t <sub>r</sub>	VDD = 30 V, 11 = 0.7 S2		165	ns		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			60	115		
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	12	20	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>				•		
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	480	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 100 A, V <sub>GS</sub> = 0 - 0.9 1.5		4 5	V		

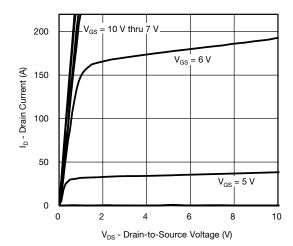
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

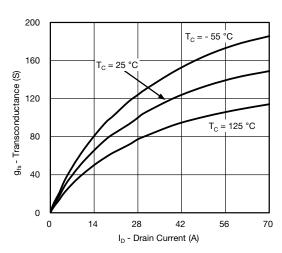
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



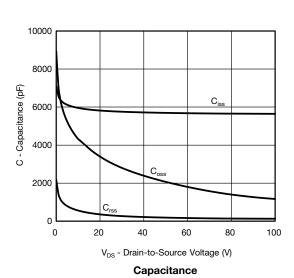
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

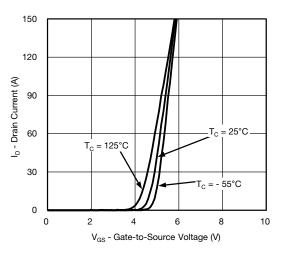


#### **Output Characteristics**

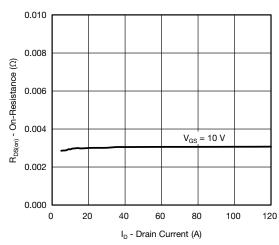


#### Transconductance

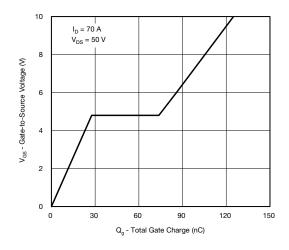




#### **Transfer Characteristics**



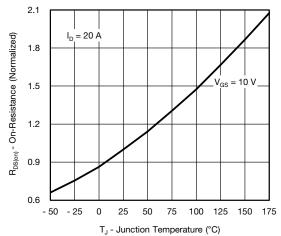
#### On-Resistance vs. Drain Current



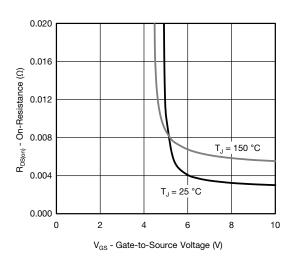
**Gate Charge** 



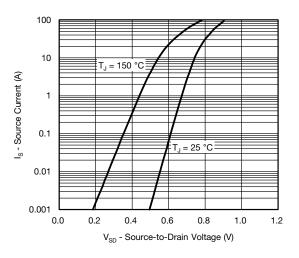
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



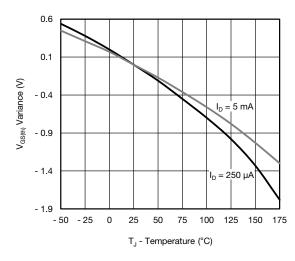
# On-Resistance vs. Junction Temperature



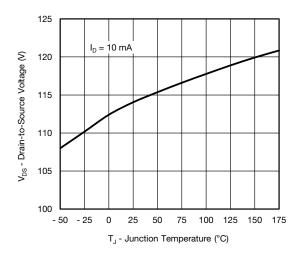
On-Resistance vs. Gate-to-Source Voltage



#### **Source Drain Diode Forward Voltage**



#### Threshold Voltage

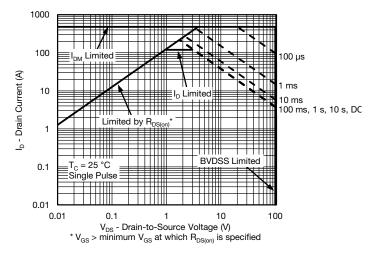


Drain Source Breakdown vs. Junction Temperature

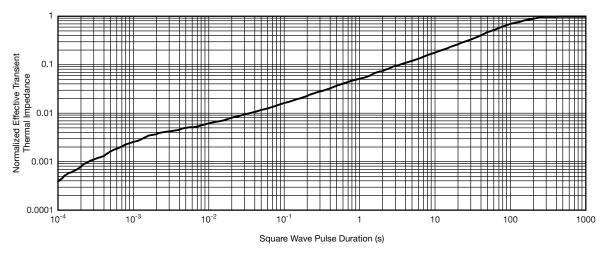
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# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



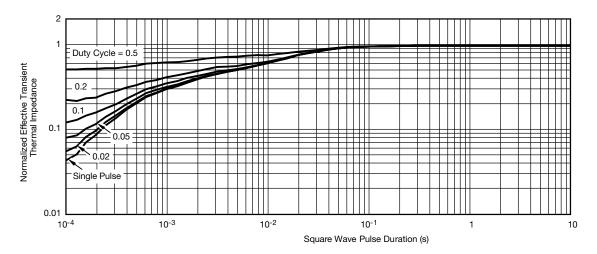
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

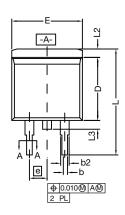
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

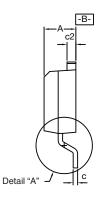
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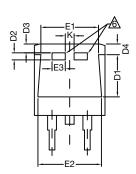
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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

#### **VERSION 1: FACILITY CODE = T**









**DETAIL A (ROTATED 90°)** 



≥ <u>↓</u>		<u> </u>	ţ
< T		10	ပ
SF	CTION	1	1

### **Notes**

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

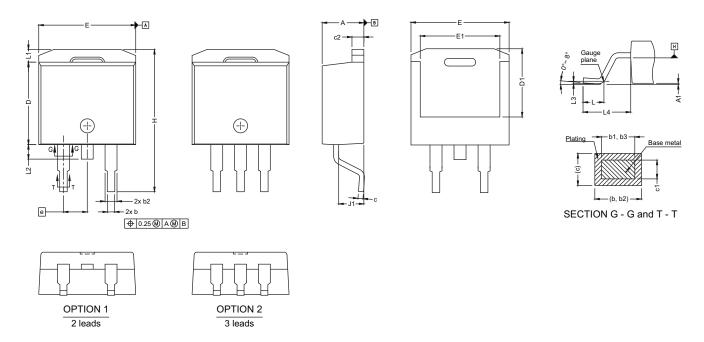
		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
C*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	<u>E1</u>	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	) BSC	2.54	BSC
K		0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
	L1	0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
	L3	0.050	0.070	1.270	1.778
	L4	0.010	BSC	0.254	BSC
	М	-	0.002	-	0.050



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### **VERSION 2: FACILITY CODE = N**



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
С	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
е	2.54	BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25	5 typ.
L4	4.78	5.28
J1	2.56	2.96

DWG: 5843





# RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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